

Approved Crystals for NanoBeacon SoC IN100

Control number: Revision: V1.2



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1. Summary

This document describes some strategies for developers to properly select and configure 26MHz crystals when developing InPlay NanoBeacon SoC IN100-based systems, explains which crystal parameters affect the system, and provides a list of several verified recommended reference crystal manufacturers and their part numbers.

Three parameters are critical to the stable operation of the IN100 based system. Figure 1 shows the IN100 default settings for the 26MHz crystal.

cycles

Figure 1: NanoBeacon Config Tool for Crystal Setting

Internal Capacitor Code: It is used for frequency bias calibration. Adjusting this value is the process of adjusting the frequency of the crystal oscillator to match to an exact reference frequency. The accuracy of the crystal oscillator depends on the accuracy of the crystal resonator itself and the temperature stability of the oscillator circuit. Note: Adjusting the capacitance value of the on-chip crystal oscillator will affect the start-up time and drive strength.

Stable Time: Crystal stabilization time is the time required for a crystal oscillator to reach its stable operating frequency after power is applied. A long stabilization time will result in longer system start-up time and will consume more power, while a short stabilization time will reduce the reliability of the system and cause the chip to fail to start. The stabilization time of a crystal oscillator is affected by various factors, such as the drive strength (the amount of current applied to the crystal), the type and size of the crystal, and the oscillator circuit design. Optimizing the crystal start-up time requires a careful balance between drive strength, crystal specifications, and oscillator circuit design.

Strength Code: The drive strength is the amount of current applied to the crystal to drive it to oscillate at its resonant frequency. A higher drive strength reduces the crystal's stabilization time, but it also increases power consumption and may damage the crystal. The optimal drive strength of a crystal oscillator depends on various factors, such as the type and size of the crystal, and the operating conditions.

This document applies to the following products:



Table 1: IN100 Product list

Applicable products	Product status
IN100-D1-R-RC1I	Mass production
IN100-D1-R-YC1I	Mass production
IN100-Q1-R-RC1I	Mass production
IN100-Q1-R-YC1I	Mass production
IN100-Q1-R-YC1F	Mass production
IN100-W10-R-SC1I	Mass production



2. Approved 26MHz Crystal

For all approved crystals, no external load caps are required. Frequency calibration only requires trimming the internal cap code of IN100. **Do not install C4 and C5** when using approved crystals.

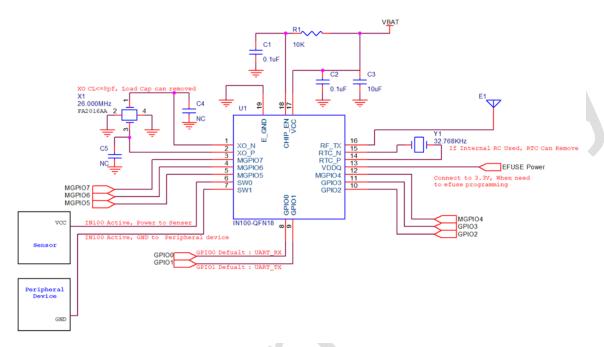


Figure 2: IN100 QFN18 reference design

The following is the list of approved crystals:

Table 2: Approved 26MHz crystals.

N o	Part number	Vender	/ender Package Size		CO	ESR	Temp Range
1	CN4026M00006BE84000 0	JWT	2.0 x 1.6 x 0.5 mm	6p F	≤2p F	≤40oh m	-40°C ~ +125°C
2	CN4026M000067A84000 0	JWT	2.0 x 1.6 x 0.5 mm	6p F	≤2p F	≤40oh m	-40°C ~ +85°C
3	XRCGE26M000FXA2AR0	Murata	2.0 x 1.6 x 0.65 mm	8p F	≤3p F	≤60oh m	-40°C ~ +125°C
4	XRCGB26M000F1SBLR0	Murata	2.0 x 1.6 x 0.7 mm	7pF	≤3p F	≤40oh m	-40°C ~ +105°C
5	ABM12L-0000-T3	Abracon	1.6 x 1.2 x 0.33 mm	8p F	≤2p F	≤80oh m	-40°C ~ +85°C
6	ABM11W-0018-T3	Abracon	2.0 x 1.6 x 0.5 mm	8p F	≤2p F	≤80oh m	-40°C ~ +85°C
7	LFXTAL081614Reel	IDQ/Wurth	1.6 x 1.2 x 0.35 mm	8p F	≤7pF	≤70oh m	-40°C ~ +85°C
8	LFXTAL082126RL3K	IDQ/Wurth	1.6 x 2.0 x 0.5 mm	8p F	≤7pF	≤25oh m	-40°C ~ +85°C

For more test result, please refer appendix A and B.



Note:

- 1* All test setups are at room temperature using IN100. 3.3V supply voltage is used.
- 2* Default settings are used for XO setting of stabilization time and drive intensity code.
- 3* Frequency is calibrated by the IN100's internal cap code

The following is the list of approved crystals XO setting for IN100. User needs to adjust according to the actual hardware situation.

Performance below was measured at the following condition with IN100 DK board: $Ta = 25^{\circ}C$, VCC = 3.0V, unless otherwise noted.

Table 3: Approved 26MHz Crystal Setting on IN100DK

No	Part number	Vender	IN100 Capacitor Code	Stable Time	Strength Code
1	CN4026M00006BE840000	JWT	5	36	16
2	CN4026M000067A840000	JWT	5	36	16
3	XRCGE26M000FXA2AR0	Murata	10	36	25
4	XRCGB26M000F1SBLR0	Murata	7	36	16
5	ABM12L-0000-T3	Abracon	11	45	16
6	ABM11W-0018-T3	Abracon	11	45	16
7	LFXTAL081614Reel	IQD/Wurth	11	36	20
8	LFXTAL082126RL3K	IQD/Wurth	10	36	18

3. Vendor Contact information

JWT

Company: HEFEI JINGWEITE ELECTRONICS CO.,LTD.

Website: http://www.hfjwt.cn

Address: No.2569, Yungu Road, Economy & Technology Area, Hefei, Anhui, China

Telephone: +86 0551-63350130,63350092

Contact: Aaron Guo Mobile: +86-156 5656 9669 Email: gxc@hfjwt.cn

Murata

Company: Murata
Website: murata.com



Telephone: +1 4082506477 Mobile: +1 4082506477 Contact: Dustin DeFrank

Email: dustin.defrank@murata.com

Abracon

Company: ABRACON LLC **Website:** <u>www.abracon.com</u>

Address: 5101 Hidden Creek Lane Spicewood, TX 78669

Telephone: +1(512)371-6159

Fax: (512) 351-8858

• IQD/Wurth

Company: Wurth / IQD Frequency Products Ltd **Website:** www.iqdfrequencyproducts.com

Address: Station Rd, Crewkerne TA18 8AR, United Kingdom

Telephone: +44 1460-270200



4. Revision History

Revision	n Description Update date		Owner
V1.0	Preliminary Version	9/1/2023	Liang X.
V1.1	Preliminary Version	9/18/2023	Aidan M.
V1.2	Updated to include latest approved xtals	10/20/2023	Aidan M.
V1.3	Updated for latest approved xtals	4/20/2024	Aidan M.

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6. Appendix A

JWT CN4026M00006T2998001 test results as follows:

頻率測试 (Measure the FREQ. of crystal on PCB board):

初始测试 (Original)

1、在PCB上测试输出频率(Measure the output frequency on PCB board)Fout1:

输出频率(Fout1) = ____25.999908 ____ MHz, __-3.54 ___ ppm

2、晶振性能测试(室温) Crystal characteristic test (at room tei 26℃

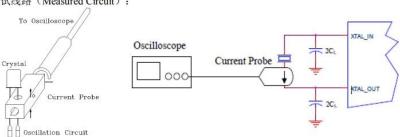
Specification(CL1) = 6 pF

FL1	FL1	Rs	C0	C1	Ts
(MHz)	(ppm)	(ohm)	(pF)	(fF)	(ppm/pF)
26.000034	1.29	18. 53	0.65	1.67	

3.
$$\triangle F = | Fout1 - FL1 | = -4.83 ppm$$

驱动功率测试 (Measure the drive level of crystal on PCB board):

1、测试线路 (Measured Circuit):



2、测试方法 (Measured Method):

使用电流探头进行Vrms测量(Tek CT-1, 50 Ω)

Use AC current probe to conduct Vrms measuring (Tek CT-1, 50 ohms terminated)

Irms = Vrms/5(mA)

3、计算方法 (Calculation Method):

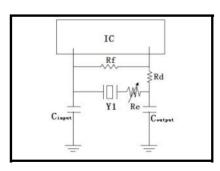
Drive Level < Data sheet Max Level Good

Drive Level ≥ Data sheet Max Level Not matching



振荡电路负阻测试(Measure the negative resistance (- R) value of chip set):

1、测试线路(Measured Circuit):



2、计算方法 (Calculation Method):

$$| -R | = Re + RL = 270$$
 + 22.76 = 292.76 ohms
 $| -R | -R | / R = 292.76$ / 40 = 7.32

n:

Poor -R value: n < 3

Normal -R value: 3 < n < 5

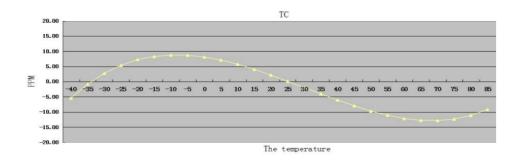
Good -R value: n > 5

RL: 负载电阻 (Load Resistance)	
R: 等效电阻 (ESR)	
Re: 可调电阻 (Variable Resistor)	

Measured oscillation characteristics

Parameter	Measured Typical Results
Work the amplitude	558 [mv]
Maximum operating amplitude	520 [mv]
Minimum operating amplitude	620 [mv]
Drive level	6.32 [uW]
The actual load capacitance	6.0 [pF]
Temperature frequency drift	See chart below
Crystal start time	0.408 [ms]

Measured frequency drift by temperature





7. Appendix B

Murata XRCGB26M000F1SBLR0 test results as follows:

Item		Condition		
IC name		IC名		IN100
Parts Number of Crystal Unit		村田型号		XRCGB26M000F1SBLR0
Circuit Parameter	External	负载电容	CL1	Open
	load capacitance	负载电容	CL2	Open
	Feedback resistance	反馈电阻	Rf	No mount
	Damping resistance	阻尼电阻	Rd	0ohm
Supply Voltage Range	电源电压范围		1.6 to 3.6V	
Temp. Range	•	温度范围		-40 to 105deg.C

Test Circuit Set : 3.3 V

7 7/1

Evaluation board : Bluetooth Rd≷ Crystal Unit ᅦ마 CL1 CL2

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Murata standard Measurement equipment

Oscilloscope DSO6052(K) CT-6(T) P5100A(T) Passive probe (40Mohm/2.5pF) DC supply E3631A(K) Sepectrum analyzer N9010A(K)

(K) Keysight (T) Tektronix

Circuit Characteristics	Value			Remarks
特性	测定值			备注
Center Frequency and Difference 起振回路上起振频率与偏差量(*1)			[MHz]	Oscillating frequency and its shift against nominal frequency 在起振回路上的频率以及相对于公称频率之间的偏差量
(Typical sample at Set=3.3V,+25deg.C)			[ppm]	
Load Capacitance on your PCB 负载容量值 (Typical sample at Set=3.3V,+25deg,C)	1		[pF]	This value shows load capacitance the evaluated circuit has 在起振回路上等价于连接在谐振器两端的容量
Negative Resistance and Oscillation margin 负性电阻/起振余裕度	-R	317	[Ω]	The details is explained in page 2 详细内容参见下页说明
(at Set=3.3V,+25deg.C)		5.3	[Times]	
Drive Level 激励功率 (Typical sample at Set=3.3V,+25deg,C)	1	1	[u W]	Drive power of crystal under circuit condition 起振回路在工作状态下谐振器消耗的功率
Oscillating Voltage 起振电压	VINp-p	0.5	[V]	Swing level at input side 输入端起振振幅 (VIN_H - VIN_L)
(Typical sample at Set=3.3V,+25deg.C)		0.5	[V]	Swing level at output side 输出端起振振幅 (VOUT_H - VOUT_L)
Oscillation Start up Time 启动时间 (*2) (Typical sample at Set=3.3V,+25deg.C)	0.	54	[ms]	Time to reach 90% of the oscillation level under steady state 达到稳定状态振幅的90%所需要时间

^{*1} Frequency difference means the oscillating frequency difference between your PCB and Murata's frequency sorting circuit. 频率偏差指在贵公司基板上的测定频率与本公司标准回路上测定频率间的偏差。
*2 The measurement results is affected by the rise-up characteristics of supplied voltage on your PCB. 测定结果受实装基板上电源启动方式的影响。



Murata XRCGE26M000FXA2AR0 test results as follows:

IC name	IC名	IN100-Q1-R-RC1I
Parts Number	品番	XRCGE26M000FXA2AR0
	Internal Capacitance Code	10
IC's setting value	Stable Time	36
	Strenght Code	25
CL1[pF]	負荷容量	Open
CL2 [pF]	負荷容量	Open
Rf [ohm]	帰還抵抗	No mount
Rd [ohm]	制限抵抗	Short
Supply Voltage Range[V]		3.3 V
Temp. Range [deg.C]	温度範囲	-40 to +125deg.C

Vdd: 3.3 V **Evaluation Board** Murata standard Measurement equipment IN100-Q1-R-RC1I DSO6052(K) Oscilloscope CT-6(T) Xin: 2 Current probe P5100A(T) Xout: 1 (40Mohm/2.5pF) E3631A(K) DC supply ≷ Rd Sepectrum analyzer N9010A(K) Crystal Unit 101 V_{out} (K) Keysight #

	//.	/ ///	,	// ///	///	
Characteristics 特性	Value 測定値			Criterion 基準	Notes 備考	
Oscillating Voltage 発振電圧		VIH	0.8	[V]	≤ 1.5V	Input high voltage 発振入力電圧High側レベル
(Vdd=3.3V,+25deg.C)	Typical sample	VIL	0.2	[V]	≥ -0.3V	Input low voltage 発振入力電圧Low側レベル
(Vcel=1.2V)	標準品	VOH	0.8	[V]	≤ 1.5V	Output high voltage 発振出力電圧High側レベル
Vcel is driving voltage of oscillation circuit Vcelは発振回路の電圧を表します		VOL	0.1	[V]	≥ -0.3V	Output low voltage 発振出力電圧Low側レベル
	R1 limit sample	VIp-p	0.5	[V]		Swing level at input side 発振入力振幅 (VIH - VIL)
	R1規格限界品(*1)	VOp-p	0.6	[V]	≥ 0.55V	Swing level at output side 発振出力振幅 (VOH - VOL)
Oscillation Start up Time 発振立ち上がり時間 (*2)		0.72	[ms]		Time to reach 90% of the oscillation level under steady state	
(Typical sample at Vdd=3.3V,+25c Center Frequency Difference 発振回路における発振周波 (Typical sample at Vdd=3.3V,+25c		-2	[ppm]		定常状態の発振振幅の90%に達するまでの時間 Oscillating frequency shift against nominal frequency 振動子の公称周波数と発振回路における 発振周波数のずれ量	
Negative Resistance Analysi 発振余裕度 (at Vdd=3.3V,+25deg.C)	8	Rs_max [Ω] 270	-R [Ω] 318	Ratio [Times] 5.3		The details is explained in page 2 詳細につきましては、次頁をご参照下さい。
Load Capacitance on your Po 負荷容量値 (Typical sample at Vdd=3.3V,+25d			8.2	[pF]		This value shows load capacitance the evaluated circuit has. 発振回路において振動子の両端に仮想的に接続される容量
Drive Level ドライブレベル (Typical sample at Vdd=3.3V,+25d		20	[uW]		Drive power of crystal under circuit condition 発振回路が動作している状態において 振動子で消費される電力	

^{**}I R1: Equivalent series resistance. "R1 limit sample" means R1 resistance of applied sample is equal as its R1 spec.
R1は振動子の等価直列抵抗を意味します。R1規格限界品とは、適用する振動子の等価直列抵抗値が、その規格値まで低下した状態のサンブルとなります。
**2 The measurement results is affected by the rise-up characteristics of supplied voltage on your PCB.
測定結果は実装基板の電源立ち上がり特性の影響を受けます。



8. Appendix C

Abracon ABM12L-0000-T3 test results as follows:

Series-Parallel resonance & motional parameters @ (+25°C ± 3°C)

Crystal Parameters			
Nominal Frequency	Fnom	26,000,000	Hz
Parallel Resonance	FL	25,999,937	Hz
Motional resistance	Rm	24.64	Ω
Motional inductance	Lm	34.17	mH
Motional capacitance	Cm	1.10	fF
Static capacitance	CO	0.91	pF

In-Circuit Frequency

Basic Oscillator Parameters			
Nominal Frequency	Fnom	26,000,000	Hz
Crystal Parallel Resonance	FL	25,999,937	Hz
Operating Frequency	F	25,999,926	Hz
Internal Capacitor Code	(0~15)	11	

Negative Resistance and Safety Factor

Basic Oscillator Parameters			
Crystal Motional resistance	Rm	24.7	Ω
Maximum Crystal Resistance	Max ESR	80	Ω
Added Series Resistance	Rs	400	Ω
Negative Resistance	I-RI	>424	Ω
Safety Factor (Ratio)	SF	>5	

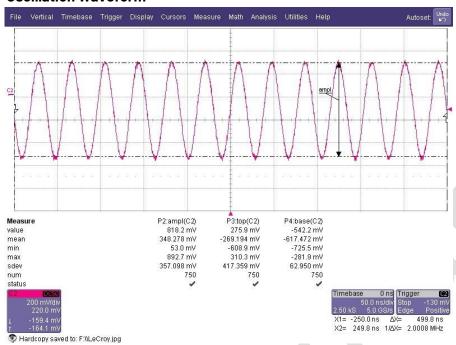
Oscillator loop continues to operate beyond an added series resistance of 400 ohms.

Drive Level

Basic Oscillator Parameters			
Crystal Effective Series Resistance	ESR	26.3	Ω
Through-Crystal Current	1	0.7	mΑ
Drive Level	DL	11.5	μW

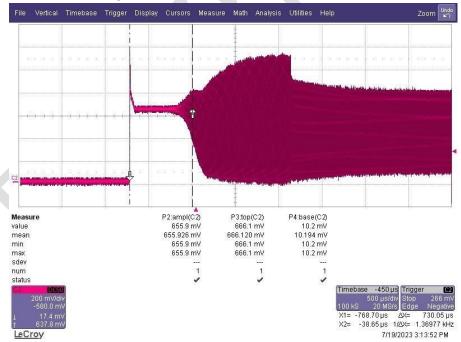


Oscillation Waveform



Passed Waveform Testing: Amplitude > 550 mV

Oscillation Start-up Waveform



Passed Startup Testing: Amplitude > 400mV in 730µs (Stable Time = 45)



9. Appendix D

IQD LFXTAL081614Reel test results as follows:

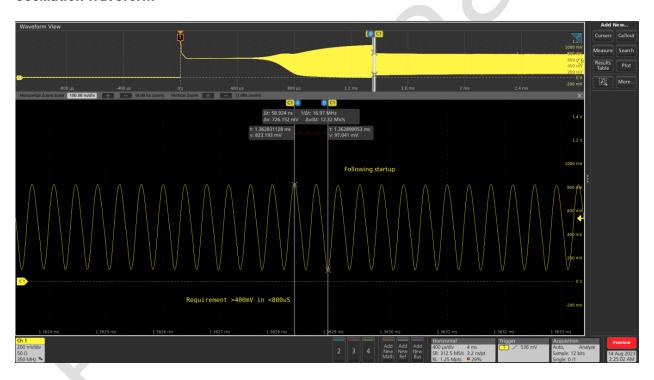
PPM Results

	Part Tested	PCB Identifier	IC Fitted	Xtal Manufacturer		Measured Frequency Hz On PCB	ΔHz	Calculated ppm deviation in circuit ppm
Ī	LFXTAL081614	PCB #1-81614	IN100	IQD	26000000.00	25999720.7636220	-279.2363780	-10.74
	LFXTAL081614	PCB #2-81614	IN100	IQD	26000000.00	25999745.9191951	-254.0808049	-9.77

$$ppm = \frac{measured \, Hz - fundamental}{fundamental \, Hz} * 1000000$$

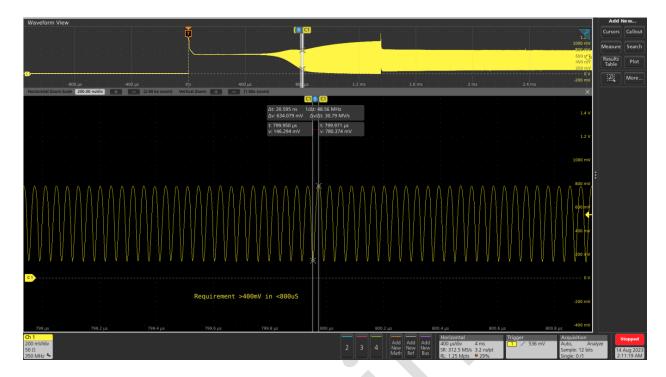
Passed BLE PPM requirements

Oscillation Waveform



Passed oscillation waveform test: Greater than 550 mV amplitude

Oscillation Startup Waveform



Passed startup requirements: 400 mV or greater amplitude in 800 us or less.

Negative Resistance Ratio and ESR:

Resistance at failure to oscillate Ohms	Neg Ratio Based	Neg R Ratio based upon Max ESR in datasheet	Max ESR from datasheet
301.20	4.30	1.51	200

Figure 8 - Negative resistance ratio with ESR measured at 70Ω

 $Negative\ resistance\ ratio = \frac{Resistance\ at\ point\ of\ poor\ startup\ or\ failure\ to\ start}{ESR\ from\ datasheet}$

It can be seen that the negative resistance ratio in this part is below 5 when we consider the maximum advertised ESR of 200Ω , however IQD historical measured data shows this part does not exceed 70Ω which gives a ratio of 4.3 times.

Passed negative resistance ratio: negative resistance ratio between 4 and 5. *Note that measured ESR by IQD was 70 Ohms, while datasheet number is an over estimate according to IQD engineer.